

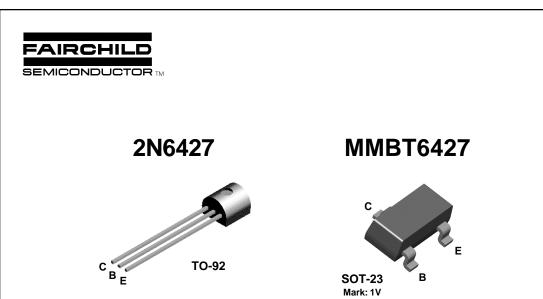
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# **ON Semiconductor**®

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## **NPN Darlington Transistor**

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	12	V
I <sub>C</sub>	Collector Current - Continuous	1.2	A
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic Max		Units	
		2N6427	*MMBT6427	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/∘C
$R_{ ext{ ext{ ext{ ext{ ext{ ext{ ext{ ext$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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# **NPN Darlington Transistor**

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(continued)

TERISTICS			·	
ector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V
ector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{E} = 0$	40		V
tter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, \ I_{C} = 0$	12		V
ector Cutoff Current	$V_{CE} = 25 \text{ V}, \text{ I}_{B} = 0$		1.0	μA
ector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		50	nA
tter Cutoff Current	$V_{EB} = 10 \text{ V}, \text{ I}_{C} = 0$		50	nA
	ector-Base Breakdown Voltage tter-Base Breakdown Voltage ector Cutoff Current ector Cutoff Current tter Cutoff Current	tter-Base Breakdown Voltage $I_E = 10 \ \mu A, I_C = 0$ ector Cutoff Current $V_{CE} = 25 \ V, I_B = 0$ ector Cutoff Current $V_{CB} = 30 \ V, I_E = 0$	tter-Base Breakdown Voltage $I_E = 10 \ \mu$ A, $I_C = 0$ 12ector Cutoff Current $V_{CE} = 25 \ V$ , $I_B = 0$ ector Cutoff Current $V_{CB} = 30 \ V$ , $I_E = 0$	tter-Base Breakdown Voltage $I_E = 10 \ \mu$ A, $I_C = 0$ 12ector Cutoff Current $V_{CE} = 25 \ V$ , $I_B = 0$ 1.0ector Cutoff Current $V_{CB} = 30 \ V$ , $I_E = 0$ 50

	$v_{EB} = 10 v, I_C = 0$		50	nA
ACTERISTICS				
DC Current Gain*	I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V	10,000	100,000	
	$I_{\rm C} = 100 \text{ mA}, V_{\rm CE} = 5.0 \text{ V}$	20,000	200,000	
	$I_{C} = 500 \text{ mA}, V_{CE} = 5.0 \text{ V}$	14,000	140,000	
Collector-Emitter Saturation Voltage	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		1.2	V
-	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		1.5	V
Base-Emitter Saturation Voltage	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		2.0	V
-				

### SMALL SIGNAL CHARACTERISTICS

Base-Emitter On Voltage

V<sub>CE(sat)</sub>

V<sub>BE(sat)</sub>

V<sub>BE(on)</sub>

C <sub>obo</sub>	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0,$ f = 1.0 MHz	7.0	pF
C <sub>ibo</sub>	Input Capcitance	$V_{BE} = 1.0 \text{ V}, I_{C} = 0,$ f = 1.0 MHz	15	pF

 $I_{C}$  = 50 mA,  $V_{CE}$  = 5.0 mA

\*Pulse Test: Pulse Width  $\leq$  300  $\mu s,$  Duty Cycle  $\leq$  2.0%

2N6427 / MMBT6427



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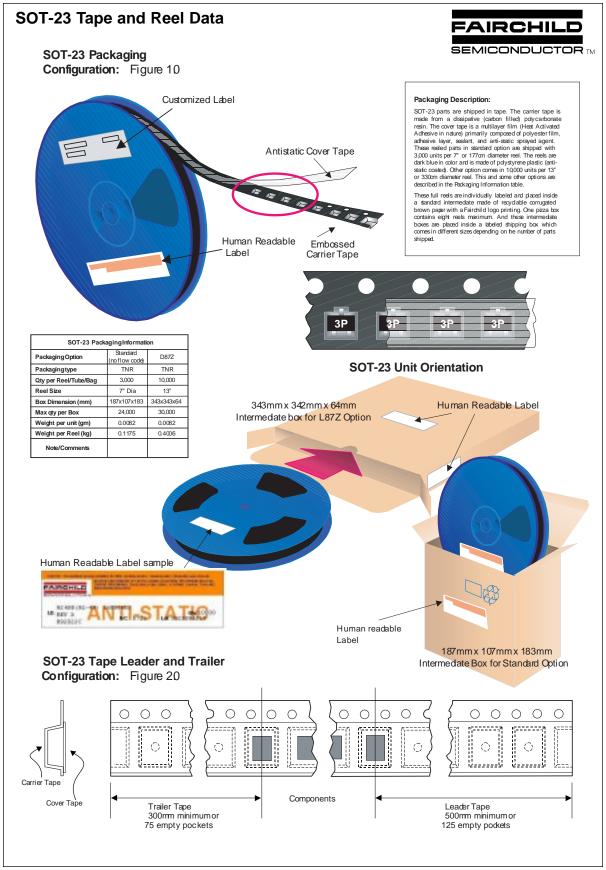
March 2001, Rev. B1





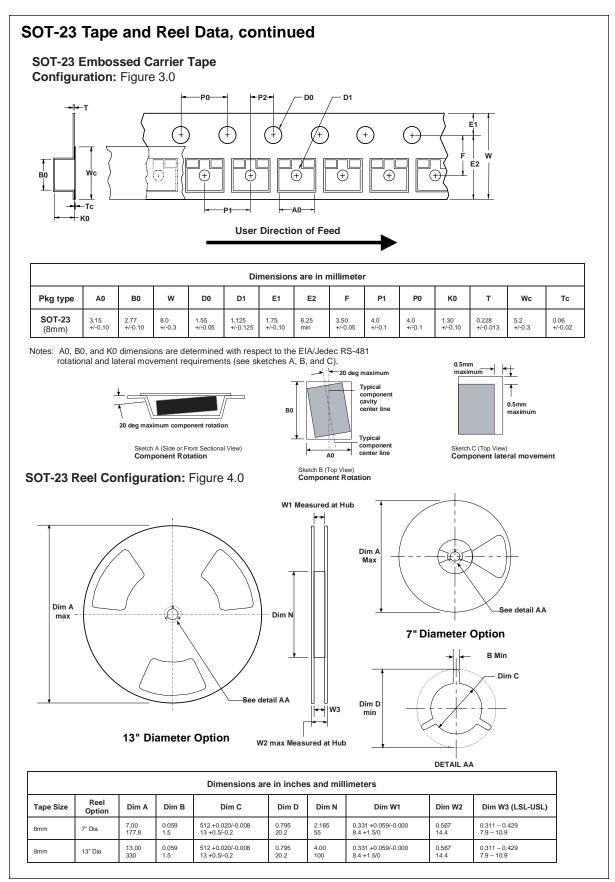
July 1999, Rev. A



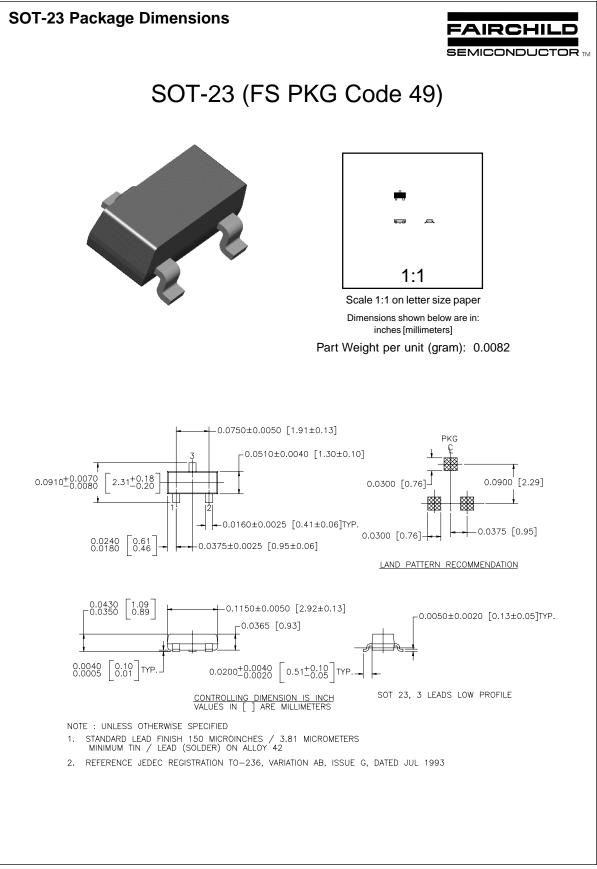


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